

FMOS1013T

List

List.....	1
Package outline.....	2
Features.....	2
Mechanical data.....	2
Maximum ratings	2
Electrical characteristics.....	3
Rating and characteristic curves.....	4~5
Pinning information.....	6
Marking.....	6
Suggested solder pad layout.....	6
Packing information.....	7
Reel packing.....	8
Suggested thermal profiles for soldering processes.....	8

FMOS1013T

-20V, -0.46A P-Channel MOSFET

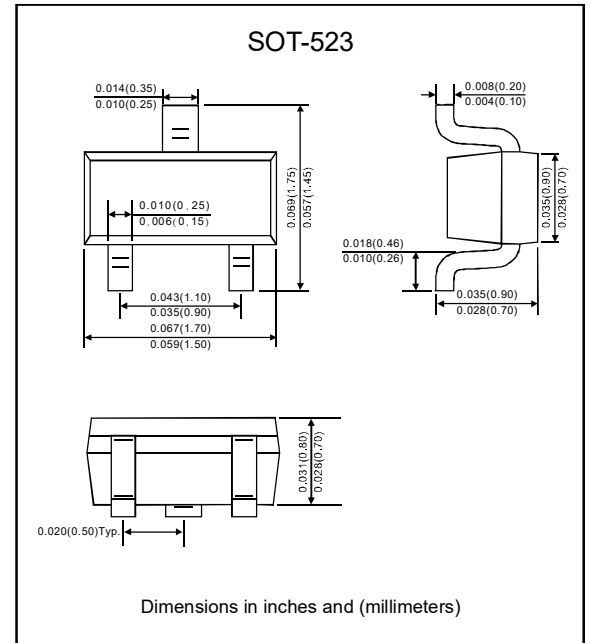
Features

- Low On-Resistance.
- Low gate threshold voltage.
- Low input capacitance.
- Fast switching speed.
- Low input / output leakage.
- ESD protected up to 3KV.
- Lead-free parts meet RoHS requirements.
- Suffix "-H" dinicates Halogen-free part, ex.FMOS1013T-H.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-523
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.003 gram

Package outline



Maximum ratings (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-source voltage	$-V_{DS}$	20	V
Gate-source voltage	V_{GS}	± 6	V
Continuous drain Current (Note 1)	$-I_D$	0.46	A
Pulsed drain current	$-I_{DM}$	6	A
Power dissipation (Note 1)	P_D	0.27	W
Operating Junction temperature range	T_J	+150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^\circ\text{C}$
Thermal resistance Junction to ambient	$R_{\theta JA}$	461	$^\circ\text{C/W}$

Notes : 1. Device mounted on FR-4 PCB.

2. No purposefully added lead.

FMOS1013T

Electrical characteristics (At $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off characteristics (Note 4)						
Drain-source breakdown voltage	-BV _{DSS}	V _{GS} =0V, -I _D =250μA	20			V
Drain-source leakage current	-I _{DSS}	-V _{DS} =20V, V _{GS} =0V			100	nA
Gate-source leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±4.5V			±2.0	μA
On characteristics (Note 4)						
Gate threshold voltage	-V _{GS(TH)}	V _{DS} =V _{GS} , -I _D =250μA	0.5		1.0	V
Static drain-source on-resistance	R _{DS(ON)}	-V _{GS} =4.5V, -I _D =350mA		0.5	0.7	Ω
		-V _{GS} =2.5V, -I _D =300mA		0.7	0.9	
		-V _{GS} =1.8V, -I _D =150mA		1.0	1.3	
Forward transfer admittance	Y _{fs}	-V _{DS} =10V, -I _D =250mA		0.9		S
Diode forward voltage (Note 4)	-V _{SD}	-I _S =150mA, V _{GS} =0V		0.8	1.2	V
Dynamic characteristics						
Input capacitance	C _{iss}	-V _{DS} =16V, V _{GS} =0V, f = 1MHz		59.76		pF
Output capacitance	C _{oss}			12.07		
Reverse transfer capacitance	C _{rss}			6.36		
Total gate charge	Q _g	-V _{GS} =4.5V, -V _{DS} =10V, -I _D =250mA		622.4		pC
Gate-source charge	Q _{gs}			100.3		
Gate-drain charge	Q _{gd}			132.2		
Switching characteristics						
Turn-on delay time	t _{d(on)}	-V _{GEN} =4.5V, -V _{DD} =10V -I _D =200mA, R _G =10Ω, R _L =47Ω		5.1		ns
Turn-on rise time	t _r			8.1		
Turn-off delay time	t _{d(off)}			28.4		
Turn-off fall time	t _f			20.7		

Notes : 4. Short duration pulse test used to minimize self-heating effect.

Rating and characteristic curves (FMOS1013T)

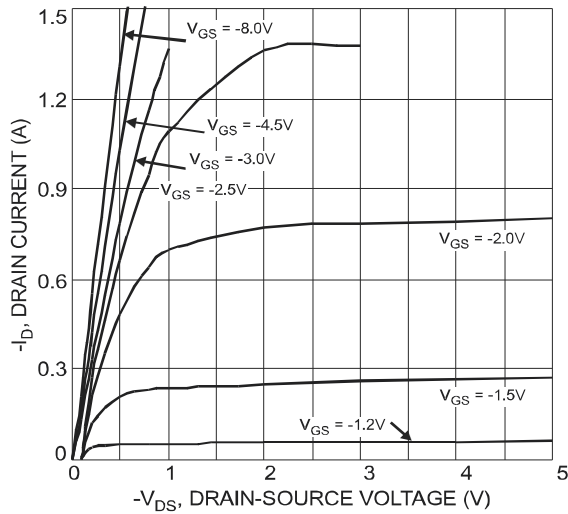


Fig. 1 Typical Output Characteristic

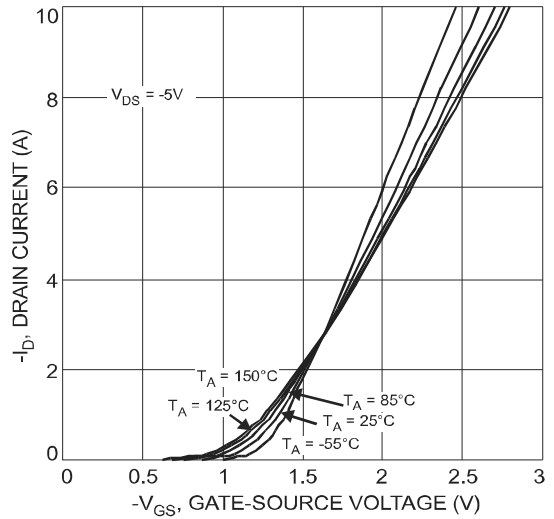


Fig. 2 Typical Transfer Characteristic

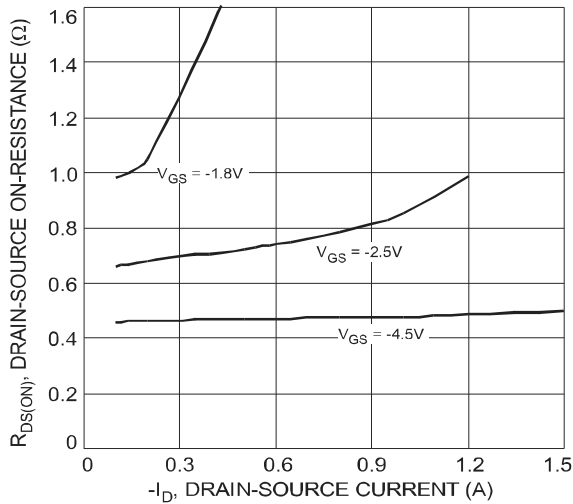


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

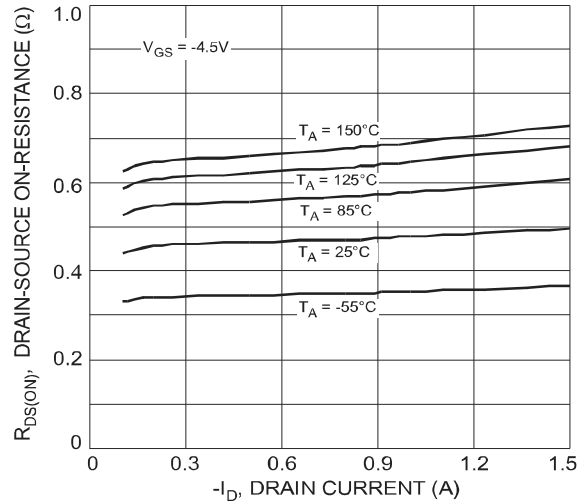


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

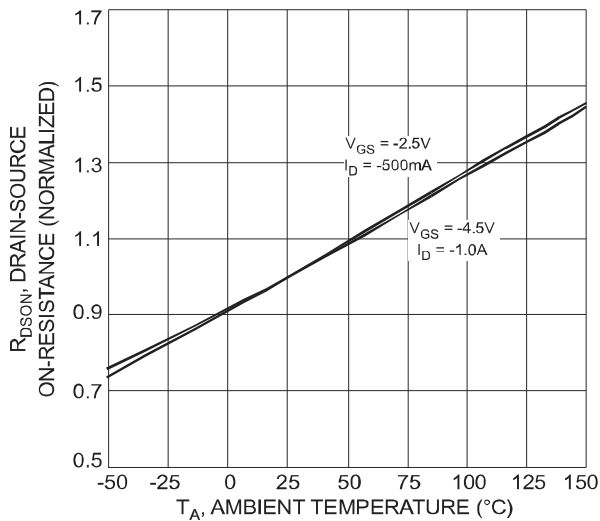


Fig. 5 On-Resistance Variation with Temperature

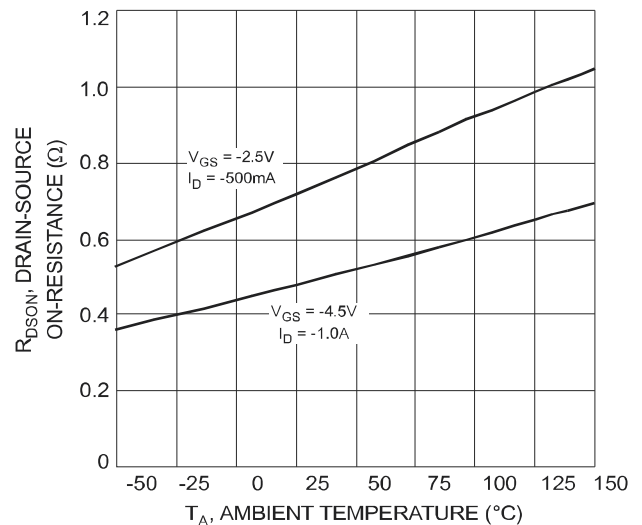


Fig. 6 On-Resistance Variation with Temperature

Rating and characteristic curves (FMOS1013T)

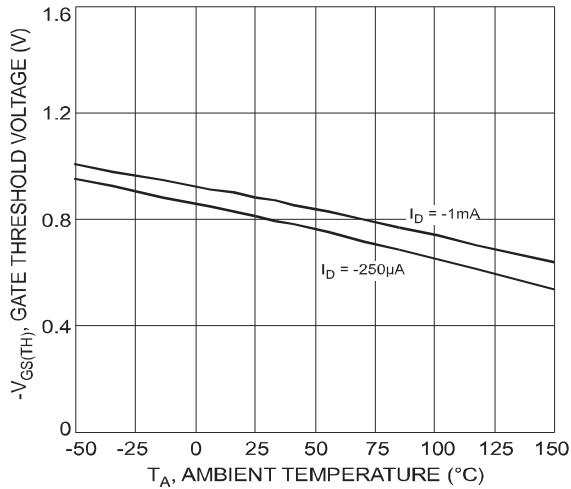


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

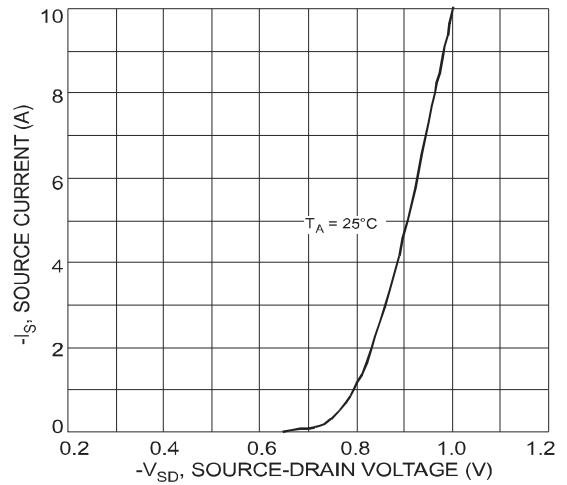


Fig. 8 Diode Forward Voltage vs. Current

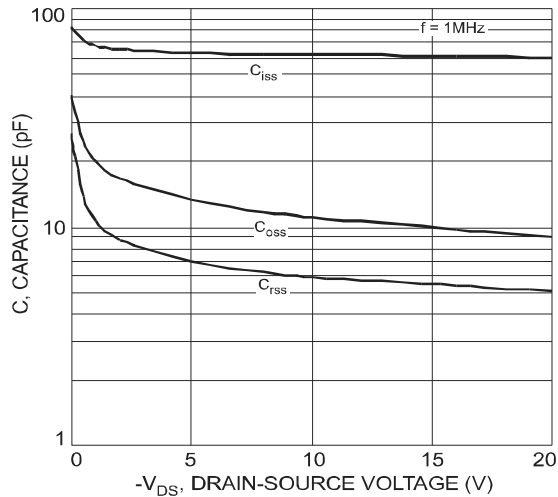


Fig. 9 Typical Total Capacitance

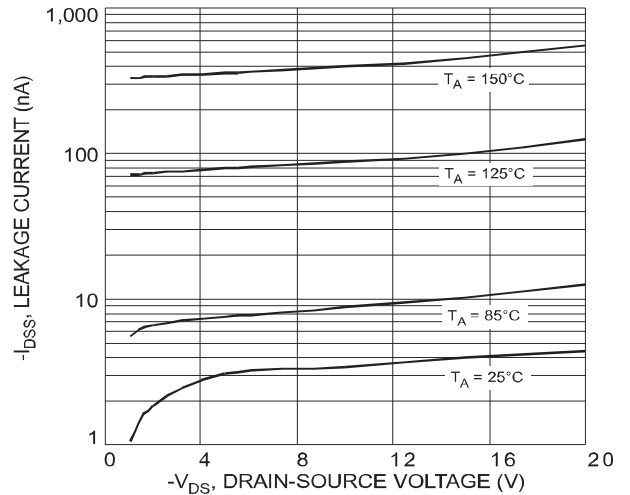


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

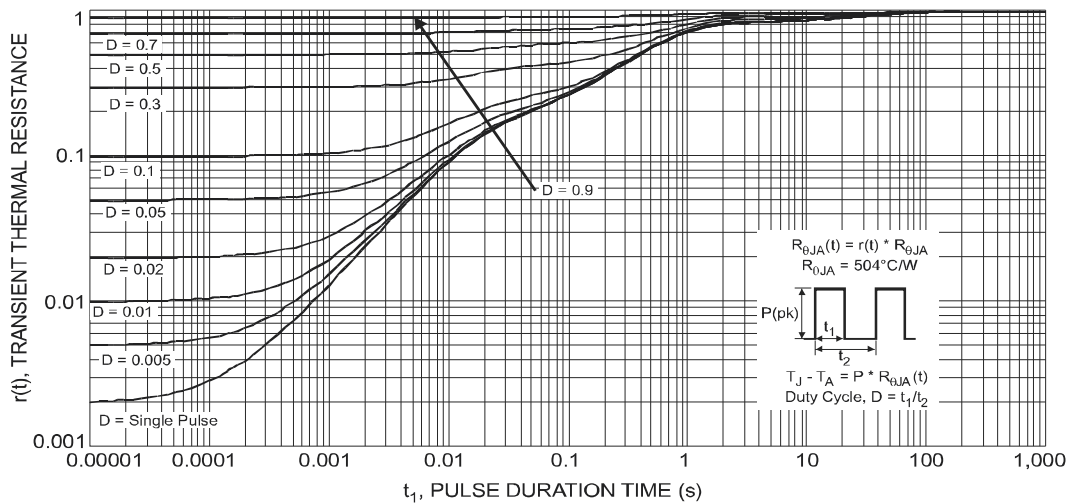
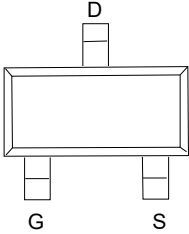
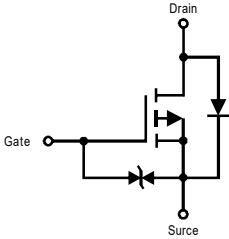


Fig. 11 Transient Thermal Response

FMOS1013T

Pinning information

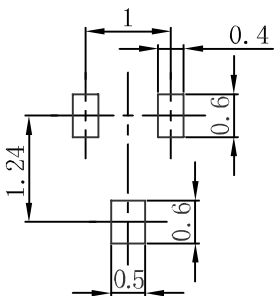
Pin	Simplified outline	Symbol
PinD Drain PinG Gate PinS Source		

Marking

Type number	Marking code
FMOS1013T	PA1

Suggested solder pad layout

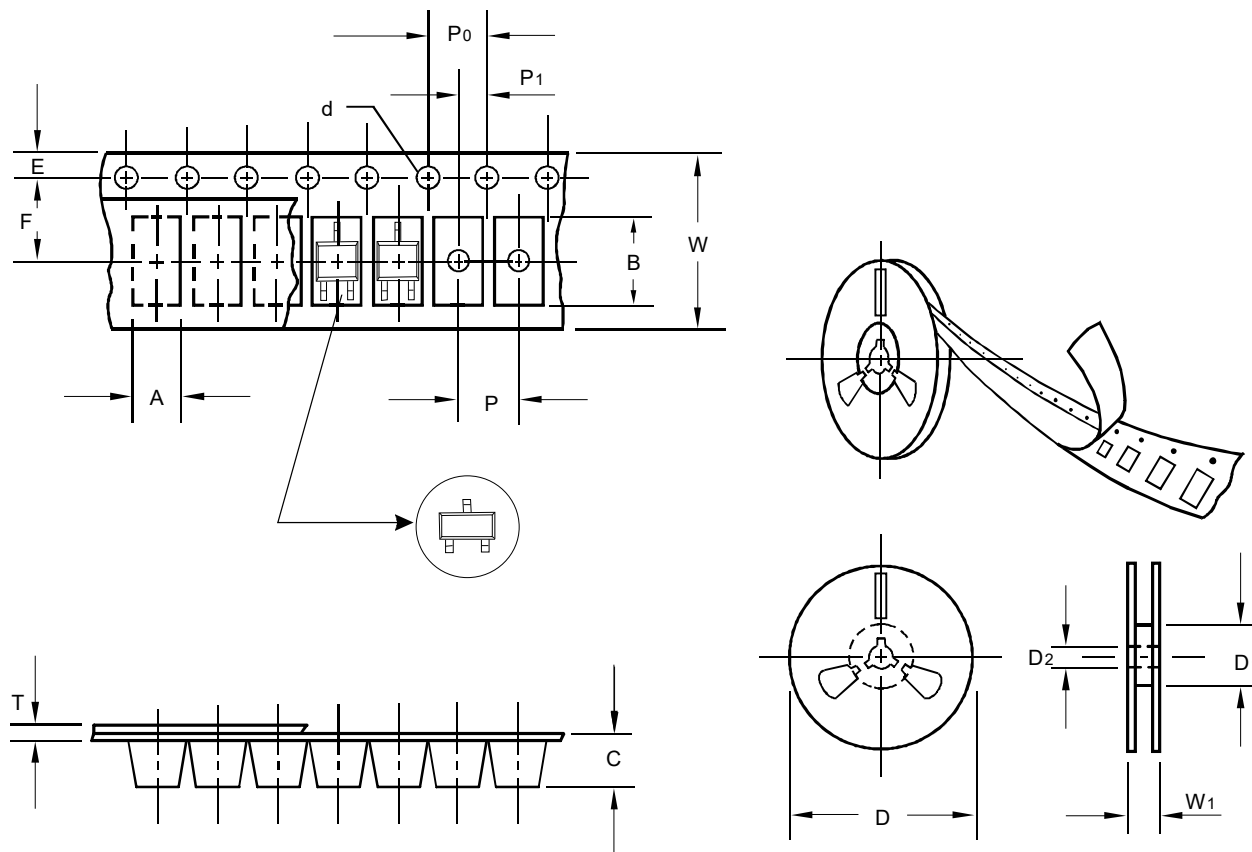
SOT-523



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

FMOS1013T

Packing information



unit:mm

Item	Symbol	Tolerance	SOT-523
Carrier width	A	0.1	1.85
Carrier length	B	0.1	1.85
Carrier depth	C	0.1	0.875
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	12.30

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

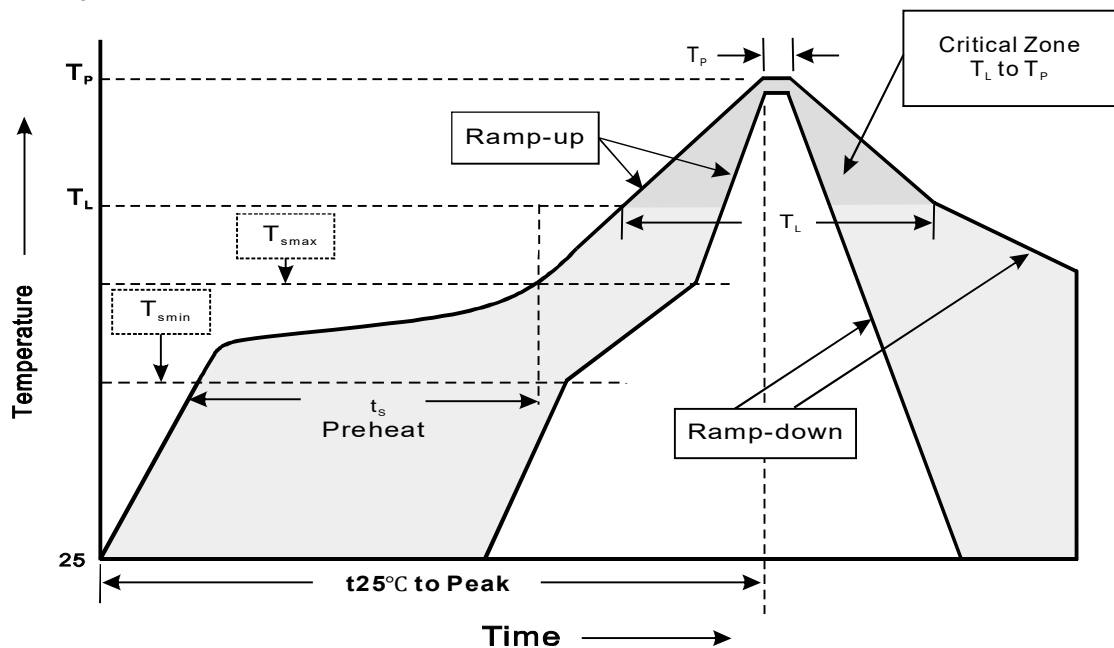
FMOS1013T

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-523	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	11.6

Suggested thermal profiles for soldering processes

- 1.Storage environment : Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile feature	Soldering Condition
Average ramp-up rate (T_L to T_P)	< 3°C/sec
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s)	150°C 200°C 60 ~ 120sec
T_{smax} to T_L - Ramp-up rate	< 3°C/sec
Time maintained above: - Temperature (T_L) - Time(T_L)	217°C 60 ~ 260 sec
Peak Temperature(T_P)	255°C -0/+5°C
Time within 5°C of actual peak Temperature(T_P)	10 ~ 30sec
Ramp-down rate	< 6°C/sec
Time 25°C to peak temperature	< 6 minutes